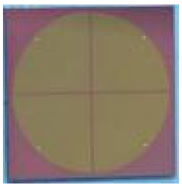
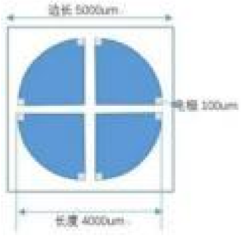
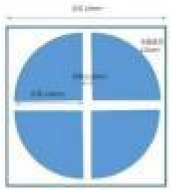
Si Quadrant PIN PD Chip datasheet

P/N : WS9I-02C







Application

Si PIN photodiode chip

Structure

Planar type : PIN diode

Electrodes :

Back side (Cathode) : Au

Top side (Anode) : Al

DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit	Notes
Active		9		mm	
Chip width		10		mm	5mm:01C 10mm:02C 16mm:03C
Chip length		10		mm	
Chip height	290	305	320	µm	
Pad Area		120		µm	

Electro-Optical Characteristics (@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.7		1.3	V
Reverse Voltage	Vbr	Ir=100µA, H=0	150			V
Reverse Dark Current	Id	Vr=50V			10	nA
Response(DC) (Quadrant)	Rei	Vr=50V	0.3			A/W
Sensitive Wavelength Range	λ		400	1064	1100	nm
Capacitance (Chip)	Cj	VR=0V, f=1MHz		150		pF